

isc Triacs

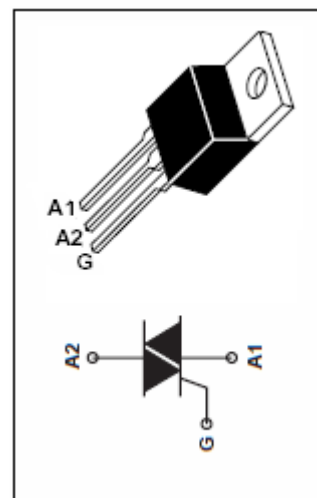
TIC216M

FEATURES

- With TO-220 package
- Sensitive Gate Triacs
- Glass Passivated
- Max I_{GT} of 5 mA (Quadrants 1~3)

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	600	V
V_{RRM}	Repetitive peak reverse voltage	600	V
$I_{T(RMS)}$	RMS on-state current (full sine wave) $T_C=70^{\circ}\text{C}$	6	A
I_{TSM}	Non-repetitive peak on-state current	60	A
T_j	Operating junction temperature	110	$^{\circ}\text{C}$
T_{stg}	Storage temperature	-45~150	$^{\circ}\text{C}$
$R_{th(j-c)}$	Thermal resistance, junction to case	2.5	$^{\circ}\text{C}/\text{W}$
$R_{th(j-a)}$	Thermal resistance, junction to ambient	62.5	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

SYMBOL	PARAMETER		CONDITIONS	MAX	UNIT
I_{DRM}	Repetitive peak off-state current		$V_D=V_{DRM}$, $T_C=110^{\circ}\text{C}$	2.0	mA
I_{GT}	Gate trigger current	I	$V_{supply} = 12\text{ V}\dagger$; $R_L = 10\ \Omega$; $t_{p(g)} > 20\ \mu\text{s}$	5	mA
		II		5	
		III		5	
		IV		10	
I_H	Holding current		$V_{supply} = 12\text{ V}\dagger$, $I_G = 0$ initial $I_{TM} = 100\text{mA}$	30	mA
V_{GT}	Gate trigger voltage	I	$V_{supply} = 12\text{ V}\dagger$; $R_L = 10\ \Omega$; $t_{p(g)} > 20\ \mu\text{s}$	2.2	V
		II		2.2	
		III		2.2	
		IV		3.0	
V_{TM}	On-state voltage		$I_T = 8.4\text{A}$; $I_G = 50\text{mA}$	1.7	V